AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1 to 21. (Canceled).

22. (Currently Amended) The component of claim 27 [[20]], wherein the anchoring element is located essentially at a center of a surface of the fixed element.

23. (Currently Amended) A [[The]] component ~~of claim 21~~, comprising:

a substrate configured as a support; and

a silicon layer in which a component structure is formed, the component structure including at least one fixed element mechanically connected to the substrate via at least one anchoring element made of an anchoring material and extending through the silicon layer,

wherein:

the silicon layer is connected to the substrate via a sacrificial layer, the fixed element mechanically connected to the substrate via at least one anchoring element extending through the silicon layer and the sacrificial layer; and

the anchoring element includes a barbed structure and extends in an area of the sacrificial layer to below the silicon layer.

24. (Currently Amended) The component of claim 23 [[21]], wherein the anchoring element includes a barbed structure and extends in an area of the sacrificial layer to below the silicon layer..

25. (Currently Amended) The component of claim 27 [[24]], wherein a surface of the electrode in at least one region around the anchoring element includes a coating made of the anchoring material.

26. (Previously Presented) The component of claim 25, wherein the coating extends essentially over an entire surface of the electrode, and at least one contact hole is formed in the coating for the electrode, the contact hole located outside the region around the anchoring element.

27. (Currently Amended) A [[The]] component ~~of claim 24~~, comprising:

a substrate configured as a support; and

a silicon layer in which a component structure is formed, the component structure including at least one fixed element mechanically connected to the substrate via at least one anchoring element made of an anchoring material and extending through the silicon layer,

wherein:

the anchoring element is configured to anchor an electrode;

the anchoring material is electrically non-conductive; and

a cap diaphragm is formed on top of the component; [[,]

the at least one electrode is electrically contacted via the cap diaphragm; and

the cap diaphragm is mechanically connected to the substrate via the anchoring element.

28. (Currently Amended) The component of claim 27 [[20]], wherein the anchoring material includes one of (a) silicon nitride and (b) silicon carbide.

29. (Canceled).

30. (Currently Amended) The method of claim 34 [[29]], wherein the recess in the silicon layer is made in the making step in an anisotropic etching process.

31. (Currently Amended) The method of claim 34 [[29]], further comprising removing the first sacrificial layer in an area of the recess in an anisotropic etching process.

32. (Currently Amended). The method of claim 34 [[31]], further comprising:

removing the first sacrificial layer in an area of the recess in an isotropic etching process;

wherein the isotropic ~~anisotropic~~ etching process includes undercutting an edge region of the recess in the silicon layer.

33. (Currently Amended) The method of claim 34 [[29]], further comprising:

depositing the anchoring material on the silicon layer to grow on the substrate in an area of the recess and fill [[fills]] the recess; and

at least partly removing an anchoring material coating of the silicon layer created by the depositing of the anchoring material.

34. (Currently Amended) A [[The]] method ~~of claim 29~~ for manufacturing a component including at least one fixed element produced in a silicon layer, the silicon layer connected to a substrate via a first sacrificial layer, ~~further~~ comprising:

(a) making at least one recess in the silicon layer in an area of a surface of the fixed element, the recess extending through the entire silicon layer and the first sacrificial layer down to the substrate;

(b) filling the recess with an anchoring material to mechanically connect the fixed element to the substrate via an anchoring element that is thereby created;

forming a cap diaphragm on the component;

producing a second sacrificial layer having a continuous surface on top of the component that is defined in the silicon layer and in which at least one electrode having the at least one anchoring element is already formed;

patterning the second sacrificial layer;

removing the second sacrificial layer in an area of the anchoring element and in an area of at least one contact point on the surface of the electrode;

producing a diaphragm layer on top of the patterned second sacrificial layer;

patterning the diaphragm layer;

creating openings for removing the second sacrificial layer;

creating openings through which an electrical connection of the electrode to the diaphragm layer is electrically insulated from remaining areas of the diaphragm layer; and

removing at least the second sacrificial layer.

35. (Previously Presented) The method of claim 34, wherein the diaphragm layer is produced in the diaphragm layer producing step from one of (a) polysilicon and (b) SiGe.

36. (Currently Amended) The method of claim 34, wherein the diaphragm layer is grown epitaxially ~~epitactically~~ from polysilicon.

37. (Previously Presented) The method of claim 36, wherein the diaphragm layer is patterned using trench etching.

38. (Previously Presented) The method of claim 34, wherein the second sacrificial layer is produced in the second sacrificial layer producing step from silicon oxide.

39. (Currently Amended) The component of claim 23 [[20]], wherein the component is configured as a sensor element.

40. (Currently Amended) The component of claim 23 [[20]], wherein the at least one fixed element includes an electrode.

41. (Currently Amended) The method of claim 34 [[29]], wherein the component is configured as a sensor element.

42. (Currently Amended) The method of claim 34 [[29]], wherein the at least one fixed element includes an electrode.

43. (Previously Presented) The method of claim 30, wherein the recess in the silicon layer is produced by trenching.

44. (Previously Presented) The method of claim 31, wherein the first sacrificial layer in the area of the recess is removed by trenching.

45. (Previously Presented) The method of claim 34, wherein openings are created for removing the second and also the first sacrificial layer.

46. (Previously Presented) The method of claim 34, wherein the second sacrificial layer is removed using HF vapor etching.

47. (New) The component of claim 27, wherein the component is configured as a sensor element.

48. (New) The component of claim 27, wherein the at least one fixed element includes an electrode.